SKYSEMI
思开半导体

# SS4407A

## 30V P-Channel MOSFET

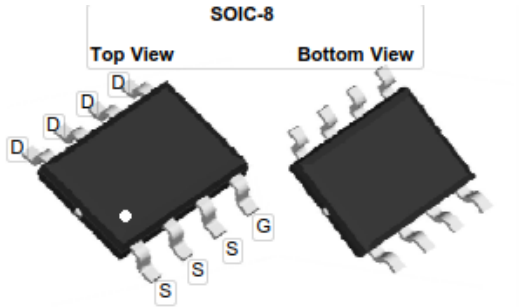
### General Description

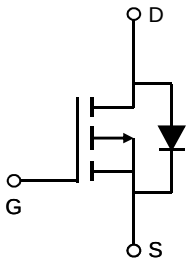
The SS4407A uses advanced trench technology to provide excellent $R_{DS(ON)}$, and ultra-low low gate charge with a 20V gate rating. This device is suitable for use as a load switch or in PWM applications.

### Product Summary

$V_{DS}$ = -30V
$I_D$ = -12A ($V_{GS}$ = -20V)
$R_{DS(ON)}$ < 13mΩ ($V_{GS}$ = -10V)
$R_{DS(ON)}$ < 17mΩ ($V_{GS}$ = -4.5V)

100% UIS Tested




**Absolute Maximum Ratings $T_A$=25℃ unless otherwise noted**

| Parameter | | Symbol | Maximum | Units |
|---|---|---|---|---|
| Drain-Source Voltage | | $V_{DS}$ | -30 | V |
| Gate-Source Voltage | | $V_{GS}$ | ±20 | V |
| Continuous Drain Current [A] | $T_A$=25℃ | $I_D$ | -12 | A |
| | $T_A$=70℃ | | -10 | |
| Pulsed Drain Current [B] | | $I_{DM}$ | -60 | |
| Avalanche Current [G] | | $I_{AR}$ | -26 | |
| Repetitive avalanche energy L=0.5mH [G] | | $E_{AR}$ | 95 | mJ |
| Power Dissipation [A] | $T_A$=25℃ | $P_D$ | 3.1 | W |
| | $T_A$=70℃ | | 2.0 | |
| Junction and Storage Temperature Range | | $T_J$, $T_{STG}$ | -55 to 150 | ℃ |

**Thermal Characteristics**

| Parameter | | Symbol | Typ | Max | Units |
|---|---|---|---|---|---|
| Maximum Junction-to-Ambient [A] | t ≤ 10s | $R_{\theta JA}$ | 32 | 40 | ℃/W |
| Maximum Junction-to-Ambient [A] | Steady State | | 60 | 75 | ℃/W |
| Maximum Junction-to-Lead [C] | Steady State | $R_{\theta JL}$ | 17 | 24 | ℃/W |